

NPN SILICON RF TRANSISTOR

DESCRIPTION:

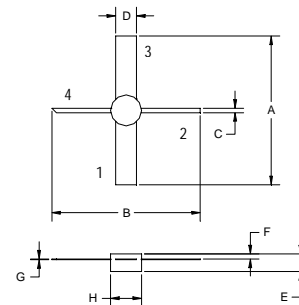
The **MRF750** is Designed for UHF Large Signal Amplifier Application from 407 to 512 MHz, and 5.0 to 10 V.

FEATURES INCLUDE:

- High Power Gain
- Infinite VSWR

MAXIMUM RATINGS

I_C	200 mA
V_{CE}	13 V
P_{DISS}	2.5 W @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	28.5 °C/W

PACKAGE STYLE .205" 4L PILL


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.00 / 25.400
B	.976 / 24.800	1.00 / 25.400
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.106 / 2.700	.139 / 3.400
F	.039 / 1.000	.047 / 1.200
G	.004 / 0.100	.006 / 0.150
H	.200 / 5.100	.208 / 5.300

1 & 3 = EMITTER 2 = BASE
4 = COLLECTOR

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 10 mA	13			V
BV_{CES}	I _C = 10 mA	25			V
BV_{EBO}	I _E = 1.0 mA	4.0			V
I_{CBO}	V _{CB} = 9.0 V			500	μA
h_{FE}	V _{CE} = 5.0 V I _C = 50 mA	20	70		---
C_{ob}	V _{CB} = 7.5 V f = 1.0 MHz		3.5	5.0	pF
G_{PE} η	V _{CC} = 7.5 V P _{out} = 500 mW fo = 470 MHz	10 55	11		dB %